Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- · High-speed line driver
- Low-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	380	mA
Static chara	acteristics		'		'	'	
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 380 mA; T_j = 25 °C		-	1.8	2.3	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



60 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
NX138BKM	DFN1006-3	plastic, leadless ultra small package; 3 terminals; 0.35 mm pitch; 1 mm x 0.6 mm x 0.48 mm body	SOT883

7. Marking

Table 4. Marking codes

Type number	Marking code
NX138BKM	6R

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	380	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	240	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	380	mW
			[1]	-	710	mW
		T _{sp} = 25 °C		-	2.8	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-draii	n diode					
Is	source current	T _{amb} = 25 °C	[1]	-	380	mA

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

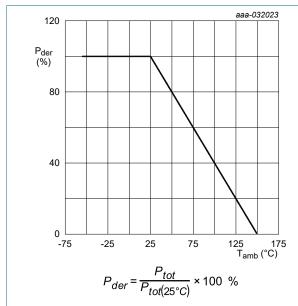


Fig. 1. Normalized total power dissipation as a function of ambient temperature

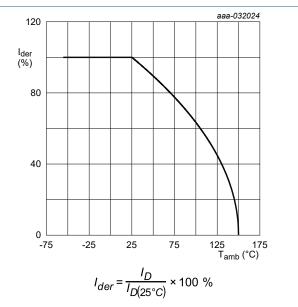


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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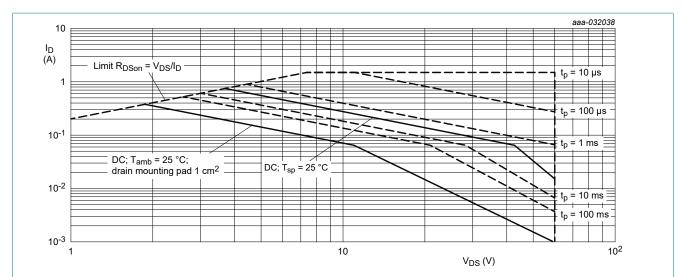


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

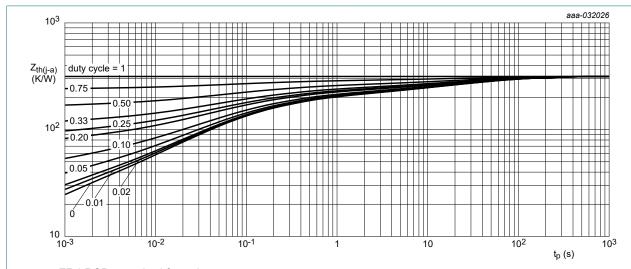
60 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

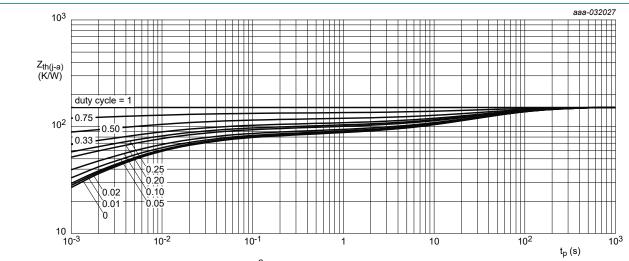
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	285	330	K/W
junction to ambient		[2]	-	150	175	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	40	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm^2

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	500	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-500	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 380 mA; T _j = 25 °C	-	1.8	2.3	Ω
		V _{GS} = 10 V; I _D = 380 mA; T _j = 150 °C	-	3.9	4.9	Ω
		V _{GS} = 5 V; I _D = 330 mA; T _j = 25 °C	-	2.2	2.9	Ω
		V _{GS} = 2.5 V; I _D = 260 mA; T _j = 25 °C	-	2.4	4.8	Ω
9 _{fs}	forward transconductance	$V_{DS} = 5 \text{ V}; I_D = 380 \text{ mA}; T_j = 25 \text{ °C}$	-	0.7	-	S
Dynamic ch	naracteristics		,	'		
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 380 \text{ mA}; V_{GS} = 10 \text{ V};$	-	0.5	0.7	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	20	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	3.1	-	pF
C _{rss}	reverse transfer capacitance		-	2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 380 mA; V _{GS} = 10 V;	-	7.9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	8.4	-	ns
t _{d(off)}	turn-off delay time	1	-	12.5	-	ns
t _f	fall time	1	-	5.1	-	ns
Source-dra	in diode		'			
V _{SD}	source-drain voltage	I _S = 380 mA; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

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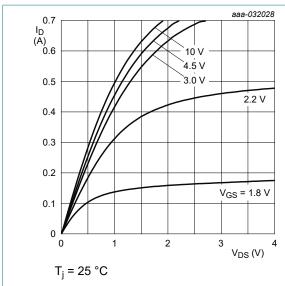


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

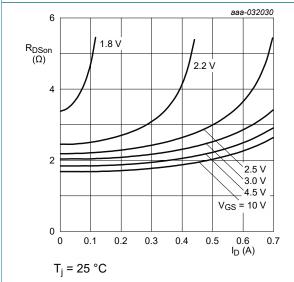


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

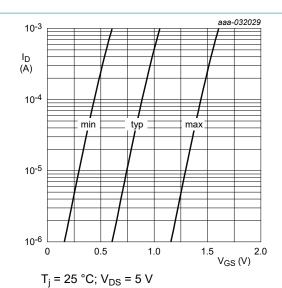


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

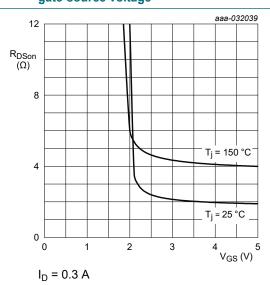


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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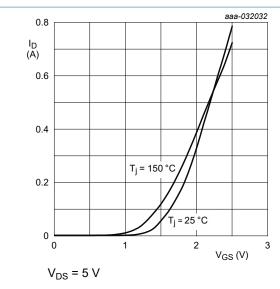


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

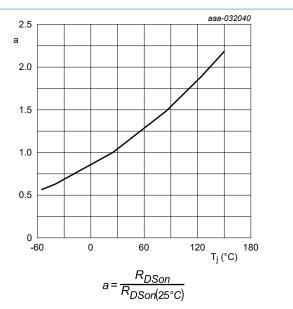


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

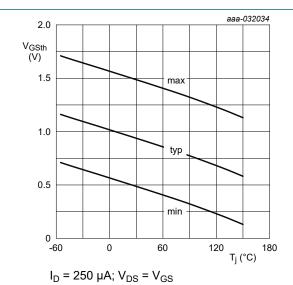
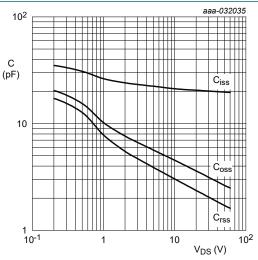


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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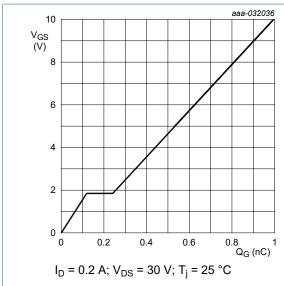


Fig. 14. Gate-source voltage as a function of gate charge; typical values

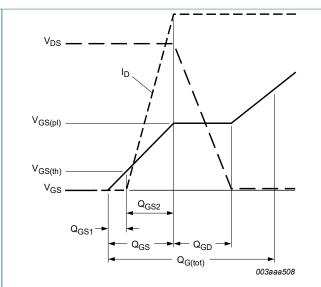


Fig. 15. Gate charge waveform definitions

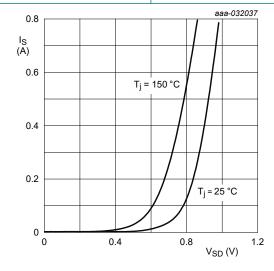
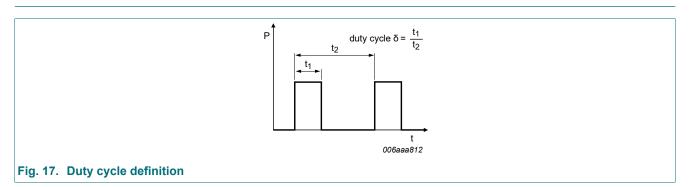


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

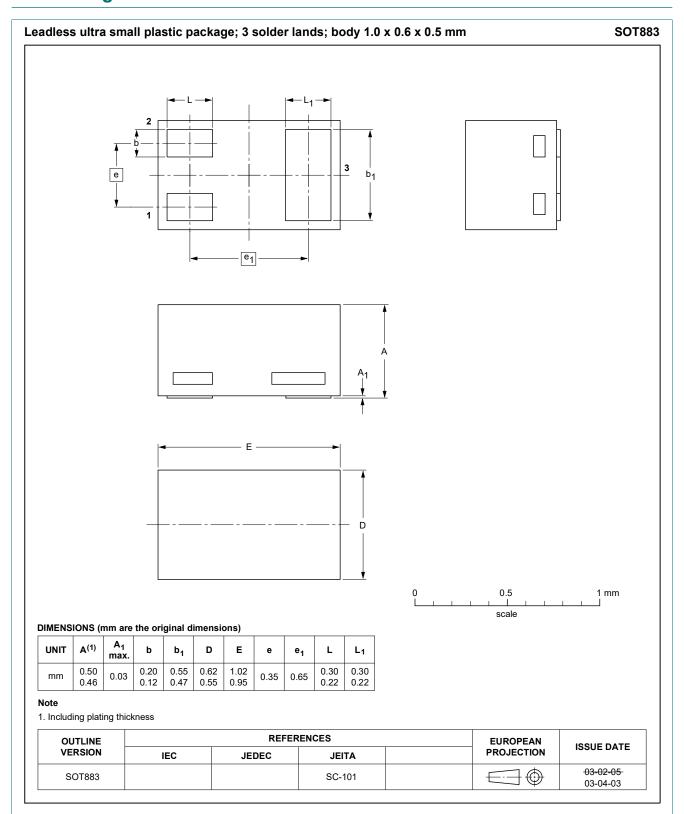
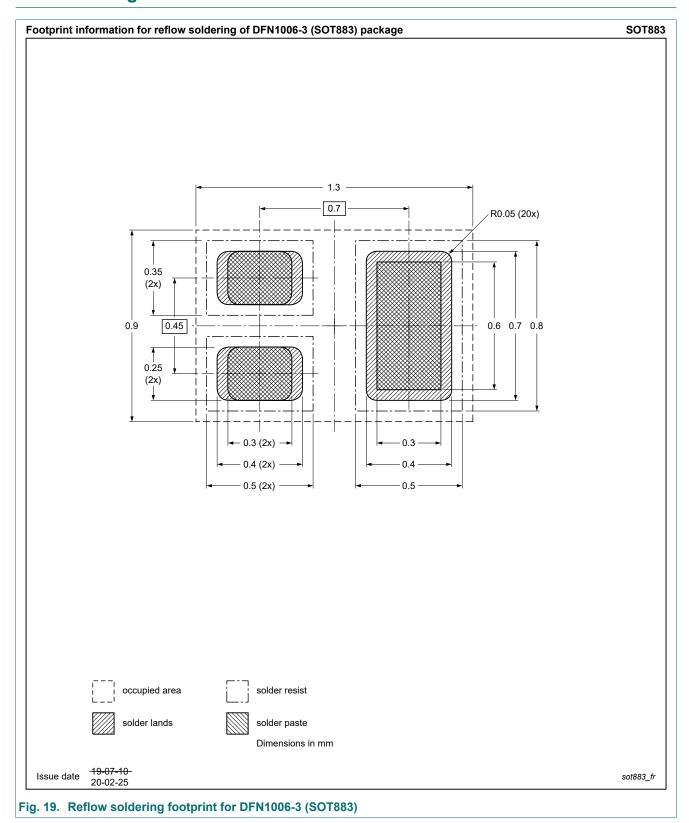


Fig. 18. Package outline DFN1006-3 (SOT883)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138BKM v.1	20200901	Product data sheet	-	-

60 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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